

ZVN4306GV

SOT223 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

Features and Benefits

- BVpss=60V
- RDS(ON) = 0.33Ω
- · Repetitive Avalanche Rating
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.112 grams (Approximate)

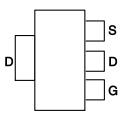
Applications

- DC-DC Converters
- Solenoids / Relay Driver for Automotive
- Stepper Motor Drivers

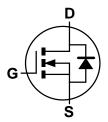




Top View



Pin Out - Top



Equivalent Circuit

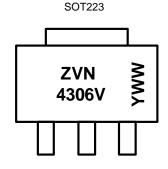
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZVN4306GVTA	ZVN4306V	7	8	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZVN4306V = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or \overline{WW} = Week Code (01~53)

February 2015

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ABSOLUTE MAXIMUM RATINGS (@TA = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I _D	2.1	Α
Pulsed Drain Current	I _{DM}	15	A
Power Dissipation	P _{tot}	3	W
Avalanche Current-Repetitive	lar	1	A
Avalanche Energy-Repetitive	Ear	25	mJ
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	ı	-	10 100	μA μA	$V_{DS} = 60V$, $V_{GS} = 0V$ $V_{DS} = 48V$, $V_{GS} = 0V$, $T = +125$ °C (Note 6)	
Gate-Body Leakage	I _{GSS}	-	1	20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
On-State Drain Current (Note 5)	I _{D(ON)}	12	-	-	Α	V _{GS} = 10V, V _{DS} = 10V	
ON CHARACTERISTICS							
Gate-Source Threshold Voltage	V _{GS(TH)}	1.3	-	3	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain Source On State Registeres (Note 5)	R _{DS(ON)}	-	0.22	0.33	Ω	$V_{GS} = 10V, I_{D} = 3A$	
Static Drain-Source On-State Resistance (Note 5)		-	0.32	0.45	Ω	$V_{GS} = 5V, I_{D} = 1.5A$	
Forward Transconductance (Notes 5 & 6)	9 _{fs}	0.7	-	-	S	$V_{DS} = 25V, I_{D} = 3A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 6)	C _{iss}	-	-	350	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	
Common Source Output Capacitance (Note 6)	Coss	-	-	140	pF		
Reverse Transfer Capacitance (Note 6)	C _{rss}	-	-	30	pF		
Turn-On Delay Time (Notes 6 & 7)	t _{D(ON)}	-	-	8	ns		
Rise Time (Notes 6 & 7)	t _R	-	-	25	ns	7	
Turn-Off Delay Time (Notes 6 & 7)	t _{D(OFF)}	-	-	30	ns	VDD ≈25V, VGEN=10V, ID=3A	
Fall Time (Notes 6 & 7)	t _F	-	-	16	ns		

DRAIN-SOURCE DIODE CHARACTERISTICS

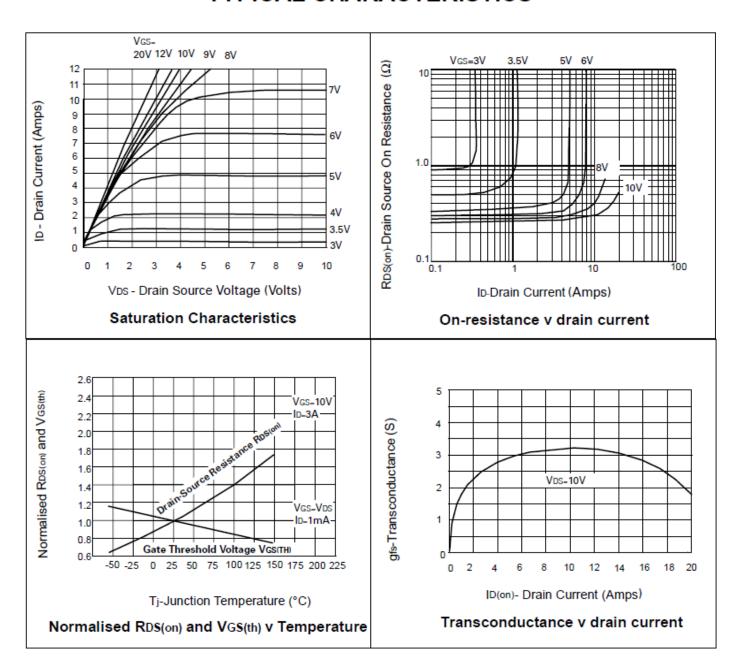
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Diode Forward Voltage (Note 5)	VsD	-	0.82	-	V	Is=0.32A, Vgs=0
Reverse Recovery Time	Trr	-	112	-	ns	IF=0.32A, Vgs=0, IR=0.1A

Notes:

- 5. Measured under pulsed conditions. Width=300 μ s. Duty cycle \leq 2%
- 6. Sample test.
- 7. Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator. Spice parameter data is available upon request for this device.

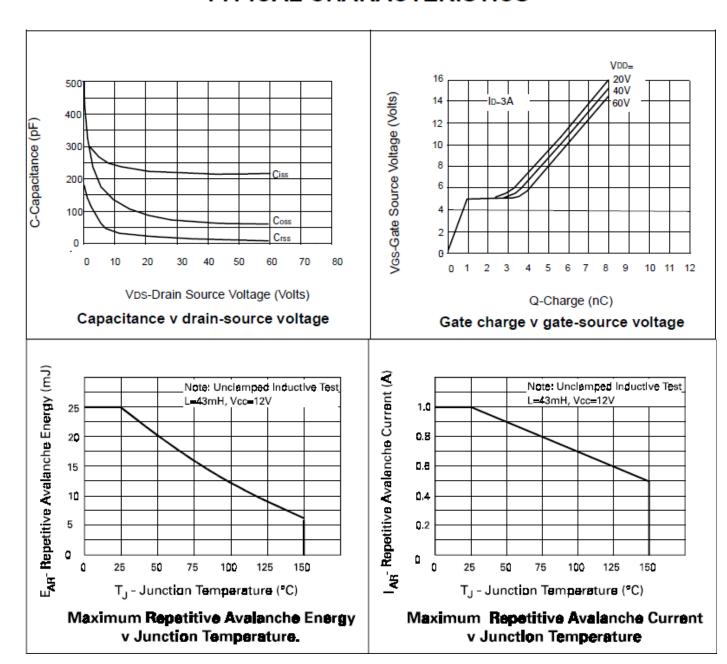


TYPICAL CHARACTERISTICS





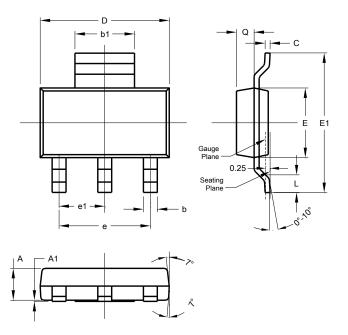
TYPICAL CHARACTERISTICS





Package Outline Dimensions

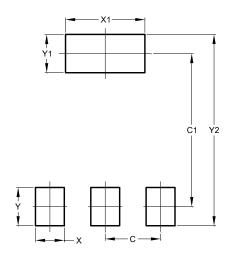
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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